

ABSTRACT OF THE DISCLOSURE

In a semiconductor device, an interlevel insulating film formed between a Cu interconnection, formed by damascene, and an upper metal interconnection layer on it
5 has a multilayered structure made up of a Cu diffusion preventive insulating layer and another insulating film. The Cu diffusion preventive insulating layer has a multilayered structure made up of not less than two layers. A method for manufacturing the semiconductor device is
10 also disclosed.

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